

KPRTR5V0U2X

Ultra Low Capacitance ESD Protection Diodes Array

DESCRIPTION

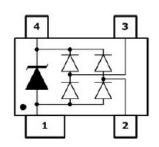
KPRTR5V0U2X provides a typical line to line capacitance of 0.6pF and low insertion loss up to 3GHz providing greater signal integrity making it ideally suited for USB 2.0 applications, such as Digital TVs, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

This device has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

ORDERING INFORMATION

Device: KPRTR5V0U2X
Package: SOT-143
Marking: SL3 or R05
Material: Halogen free
Packing: Tape & Reel
Quantity per reel: 3,000pcs

PIN CONFIGURATION



FEATURES

- ♦Protects two I/O lines and one Vcc line
- ♦Low capacitance
- ♦Low leakage current
- ♦No insertion to 3.0 GHz
- ♦5V operating voltage
- ♦Response time < 1ns
- ♦ Solid-state silicon avalanche technology
- ♦ Device meets MSL 1 requirements
- ♦RoHS compliant

MACHANICAL DATA

- ♦SOT-143 package
- ♦ Flammability Rating: UL 94V-0
- ♦ Terminal: Matte tin plated.
- ♦ Packaging: Tape and Reel
- ♦High temperature soldering guaranted:260 °C /10s
- ♦Reel size: 7 inch

APPLICATIONS

- **♦**xDSLI
- **♦USB 1.1/2.0/OTG**
- ♦IEEE 1394 Firewire Ports
- ♦ Notebooks & Handhelds
- ♦ Projection TV & Monitors
- ♦ Set-top box
- ♦Flat Panel Displays

PACKAGE OUTLINE







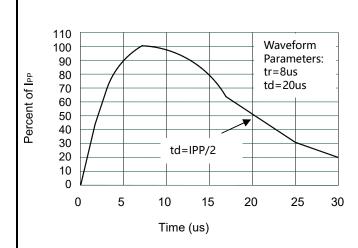
ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
P _{PP}	Peak Pulse Power (8/20µs)	125	W				
I _{PP}	Peak Pulse Current (8/20µs)	5	А				
V _{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±15 ±8	kV				
T _{OPT}	Operating Temperature	-55/+150	°C				
T _{STG}	Storage Temperature	-55/+150	°C				

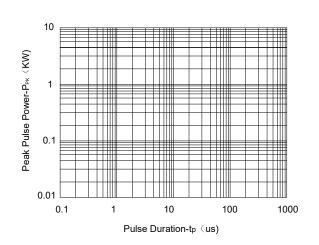
ELECTRICAL CHARACTERISTICS (Tamb=25°C)									
Symbol	Parameter	Test Condition	Min	Тур	Max	Units			
V_{RWM}	Reverse Working Voltage	Any I/O pin to GND			5.0	V			
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA Any I/O pin to GND	6.0			V			
I _R	Reverse Leakage Current	V _{RWM} = 5V Any I/O pin to GND			1	μΑ			
V_{F}	Diode Forward Voltage	I _F = 15mA		0.85	1.2	V			
V _{C1}	Clamping Voltage 1	I_{PP} = 1A, t_p = 8/20µs Any I/O pin to GND			15.5	V			
V_{C2}	Clamping Voltage 2	I _{PP} = 5A, t _p = 8/20μs Any I/O pin to GND			25	٧			
I _{PP}	Peak Pulse Current	t _p = 8/20µs Any I/O pin to GND			5	Α			
C _{J1}	Junction Capacitance 1	V _R = 0V, f = 1MHz Between I/O pins		0.45	0.6	pF			
C_{J2}	Junction Capacitance 2	$V_R = 0V$, $f = 1MHz$ Any I/O pin to GND		0.9	1.2	pF			

Note: I/O pins are pin2,3.



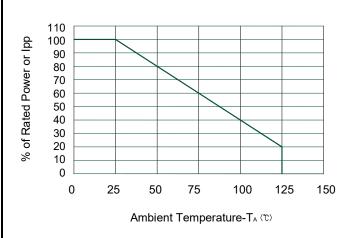
ELECTRICAL CHARACTERISTICS CURVE

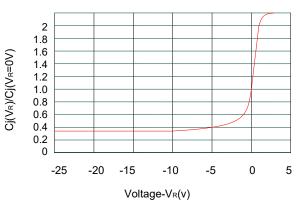




Pulse Waveform

Non-Repetitive Peak Pulse Power vs. Pulse Time





Power Derating Curve

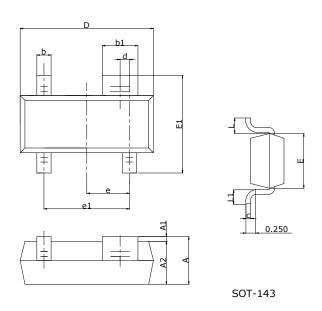
Junction Capacitance vs. Reverse Voltage





Ultra Low Capacitance ESD Protection Diodes Array

SOT-143 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	MIN	MAX	
Α	0.90	1.15	0.035	0.045	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.05	0.035	0.041	
b	0.30	0.50	0.012	0.020	
b1	0.75	0.90	0.030	0.035	
С	0.08	0.15	0.003	0.006	
D	2.80	3.00	0.110	0.118	
d	0.20TYP		0.008TYP		
E	1.20	1.40	0.047	0.055	
E1	2.25	2.55	0.089	0.10	
е	0.95TYP		0.037TYP		
e1	1.80	2.00	0.071	0.079	
L	0.55REF		0.022REF		
L1	0.30	0.50	0.012	0.020	